

Descriptions

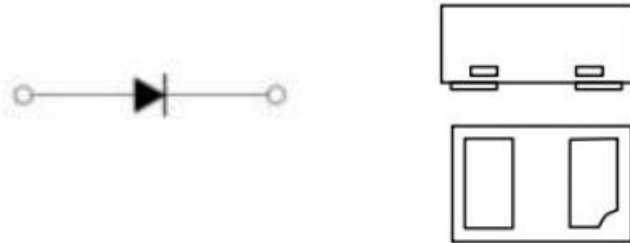
The CT140ZP is schottky barrier diode, DFN1006-2L plastic package

Features

- Low forward voltage drop
- Very small surface mounting packages
- Low voltage rectification
- High efficiency DC/DC conversion
- Inverse polarity protection
- Low power consumption application

V_{RM}	I_O	I_{FSM}
40 V	1A	7 A

Equivalent Circuit & Pinning



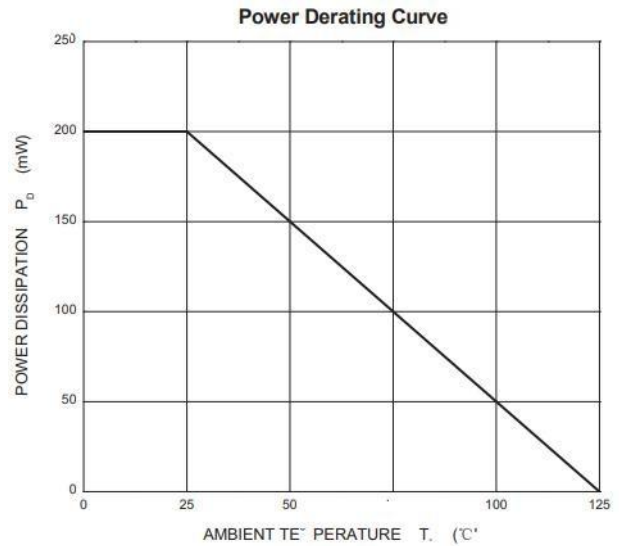
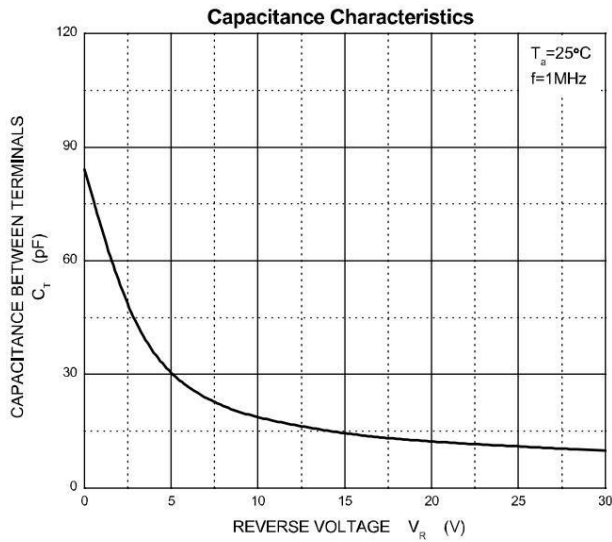
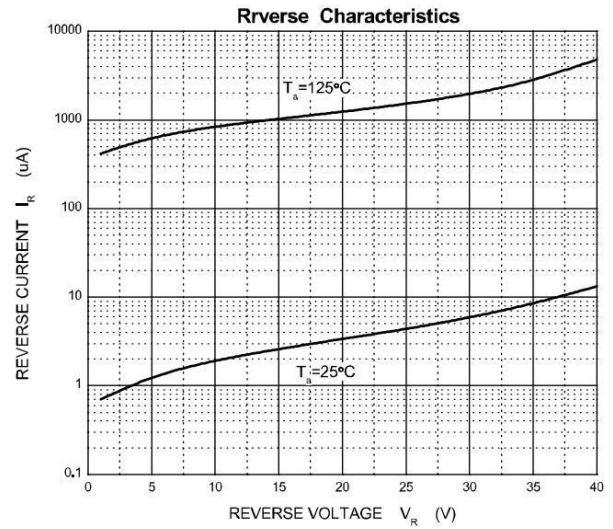
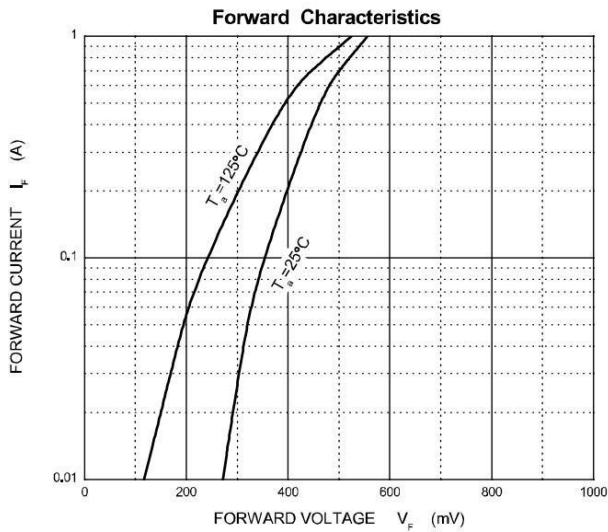
Absolute Maximum Ratings(Ta=25°C)

Parameter	Symbol	Limit	Unit
Peak Reverse Voltage	VRM	40	V
Work Peak Reverse Voltage	VRWM	40	
RMS Reverse Voltage	VR(RMS)	28	
Average Rectified Output Current	IO	1	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	IFSM	7	A
Power dissipation	Pd	500	mW
Thermal resistance junction to ambient	RθJA	250	°C /W
Operating Junction Temperature Range	TJ	-40~125	°C
Storage Temperature Range	TSTG	-55~155	°C

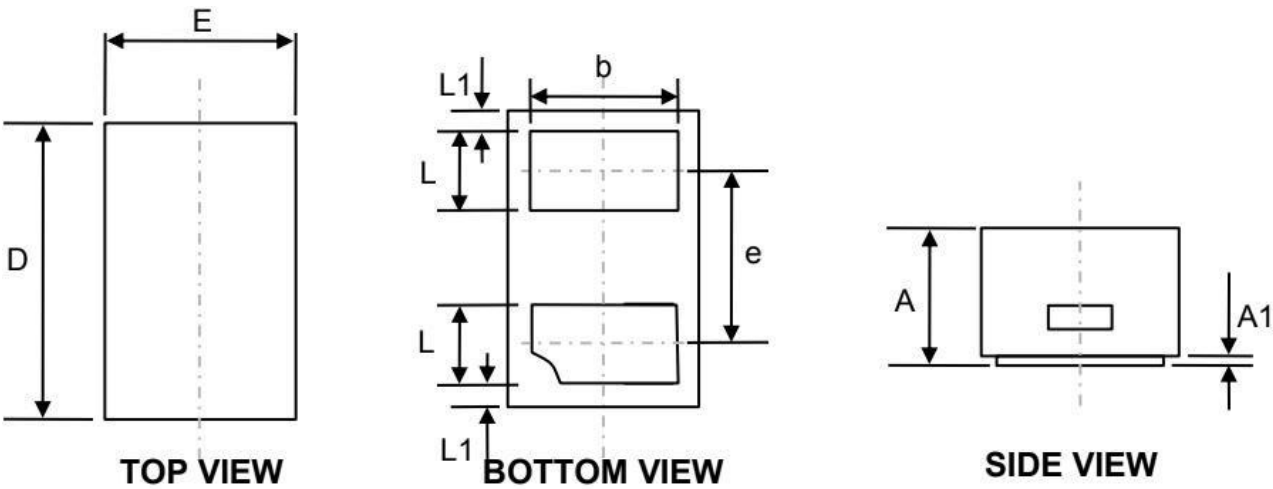
Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	MS10N40			Unit
			Min	Typ	Max	
Reverse breakdown voltage	V(BR)	IR=1mA	40			V
Forward voltage	VF	IF=100mA		0.35	0.38	V
		IF=200mA		0.37	0.40	V
		IF=500mA		0.48	0.49	V
		IF=1A		0.59	0.62	V
Reverse current	IR	VR=40V		10	40	uA
Capacitance between terminals	CT	VR=0V, f=1MHZ		19	25	pF

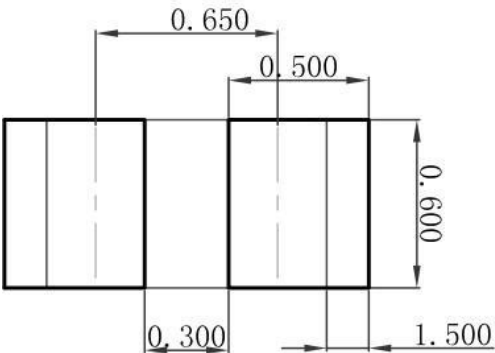
Electrical Characteristic Curve



Package Outline Dimensions



Symbol	Dimensions In Millimeters (mm)		
	Min.	Typ.	Max.
A	0.44	0.47	0.50
A1	0.00	0.03	0.05
D	0.95	1.00	1.08
E	0.55	0.60	0.68
b	0.40	0.50	0.60
e	-	0.65	-
L	0.20	0.25	0.30
L1	0.05 REF.		



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.050mm.
3.The pad layout is for reference purposes only.